

FIG. 1A

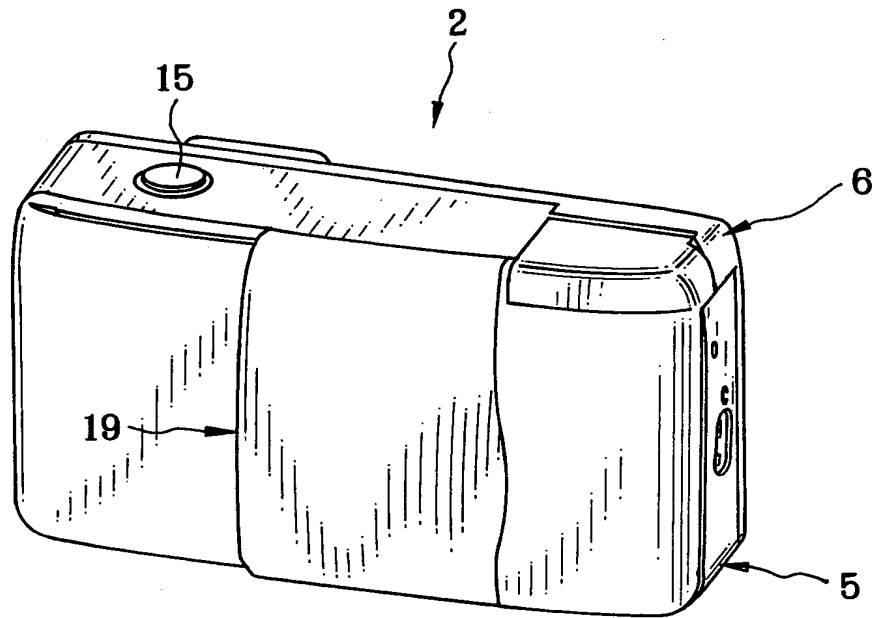


FIG. 1B

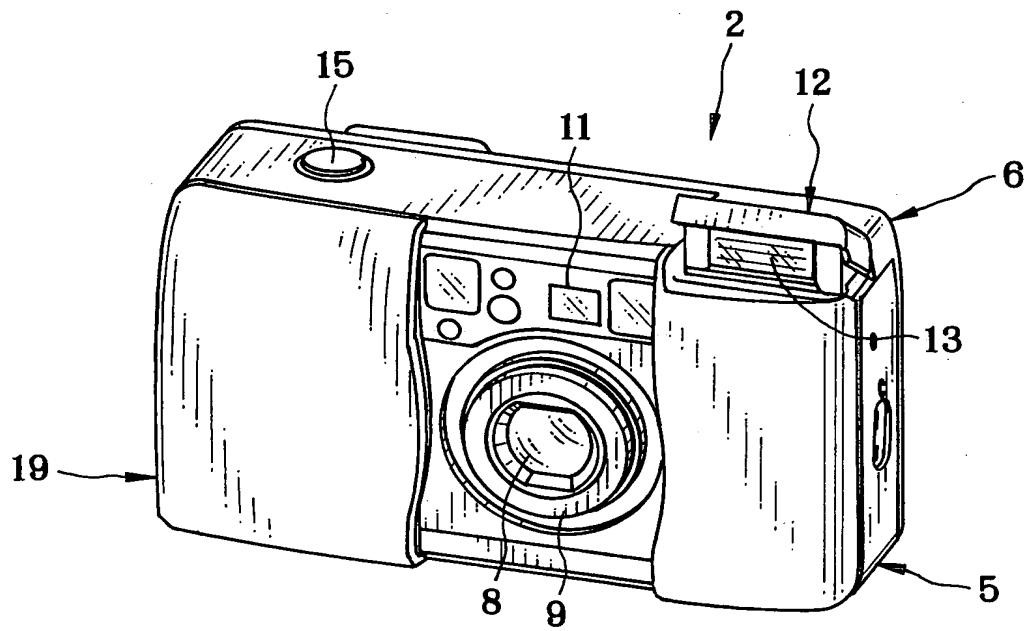


FIG. 2

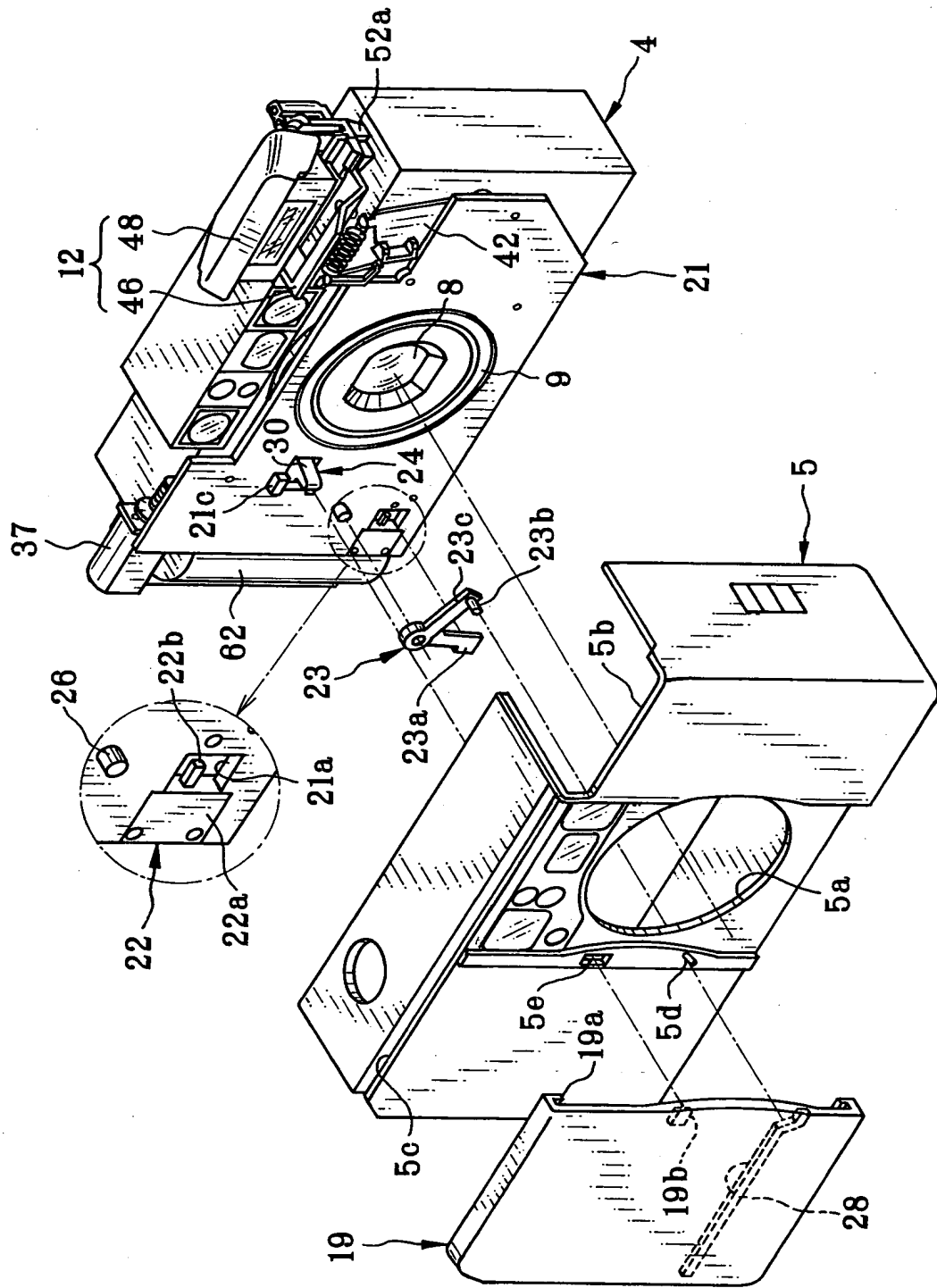


FIG. 3

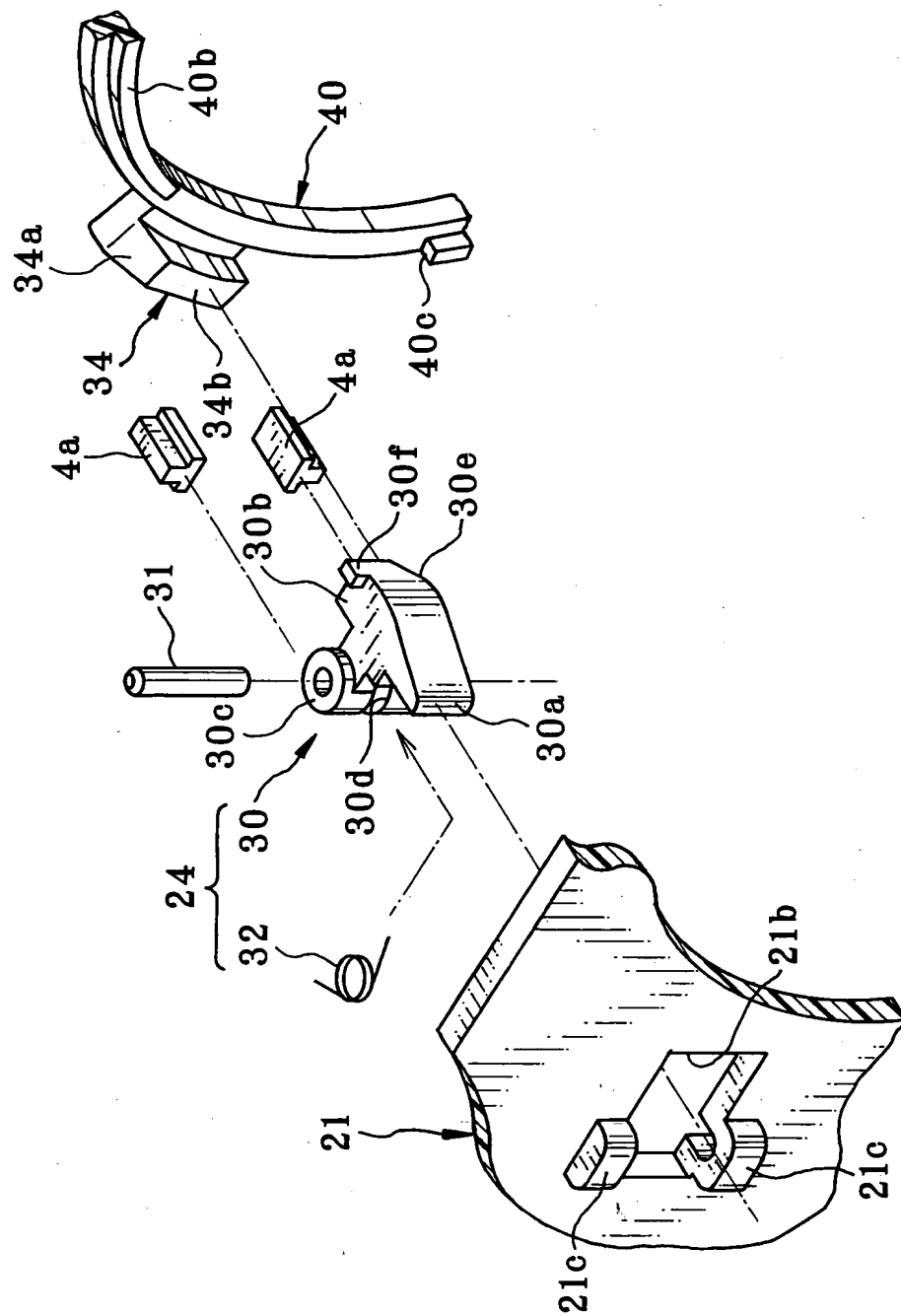


FIG. 4A

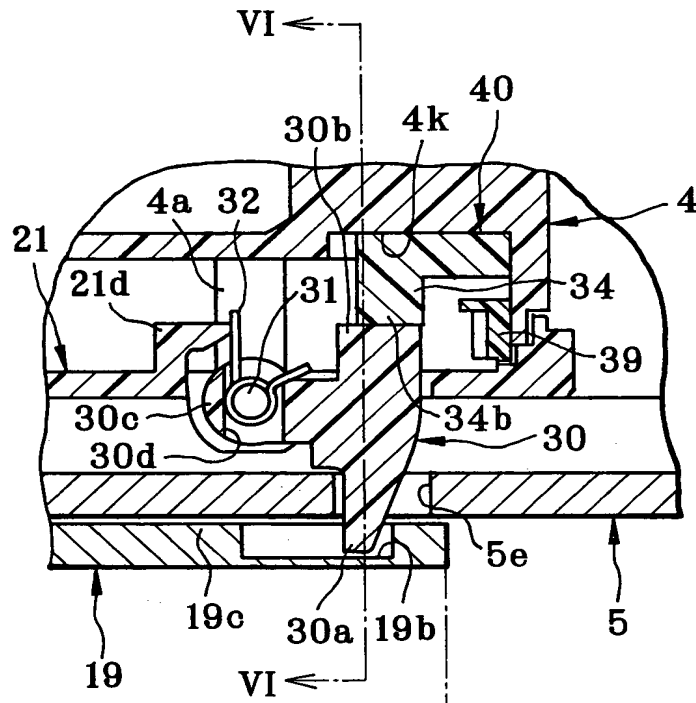


FIG. 4B

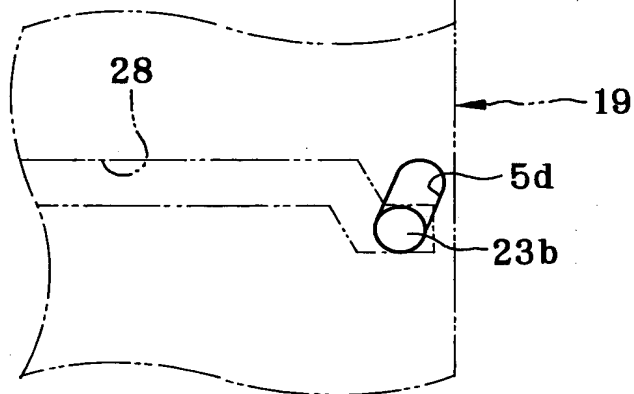


FIG. 5

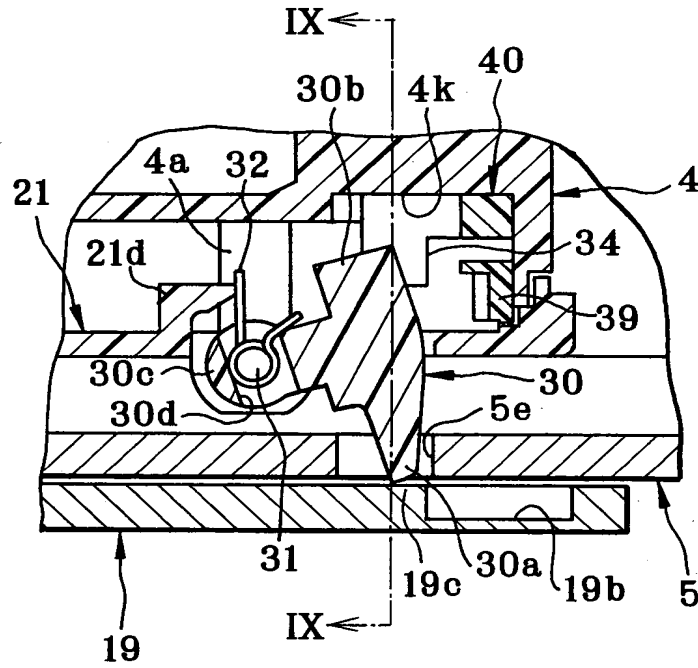


FIG. 6

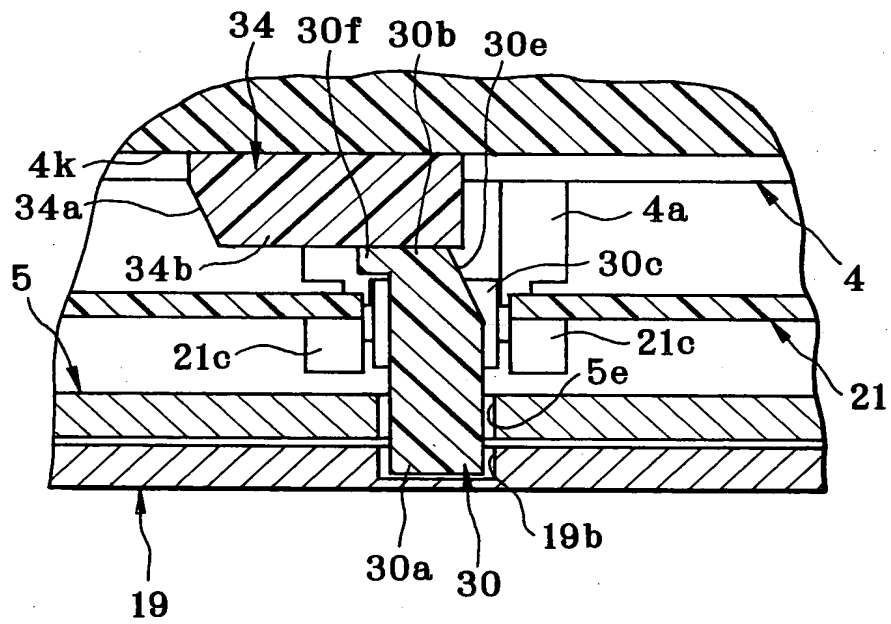


FIG. 7A

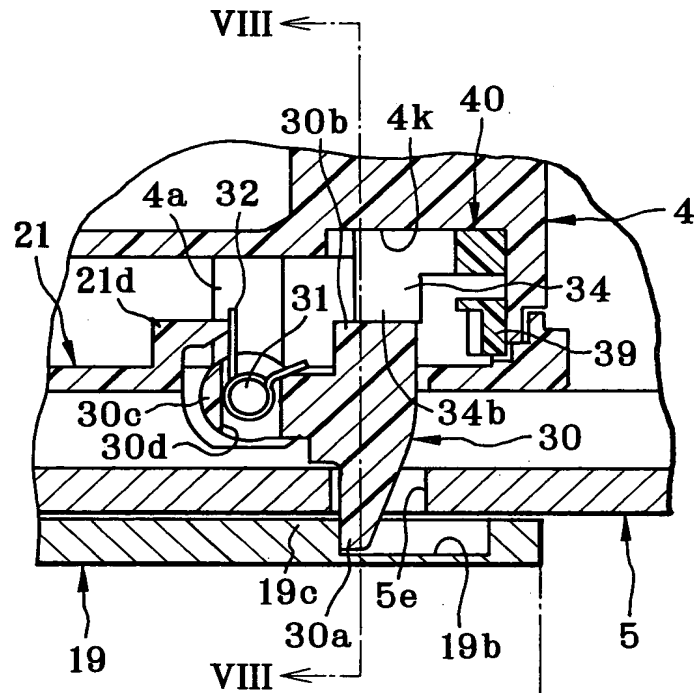
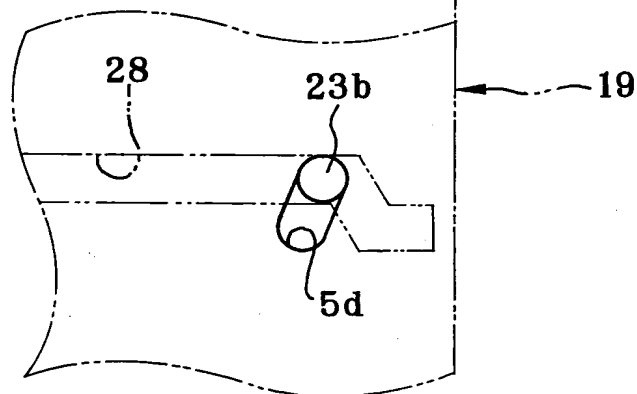


FIG. 7B



[illegible]

This diagram illustrates a second embodiment of the semiconductor device in cross-section. The structure features a substrate 19 at the base, followed by a layer 19c. Above this is a stack of layers including 30a, 30, and 30f. A central vertical feature is labeled 30b. To the left, there is a component labeled 4k above a block 4a, which sits on a layer 5. Below 4a is a layer 21c. To the right, a similar structure includes a block 34b above a layer 30e, which sits on a layer 5e. This is further supported by a layer 21. The topmost layer is labeled 34. Various hatching patterns are used to distinguish different materials or regions.

FIG. 10

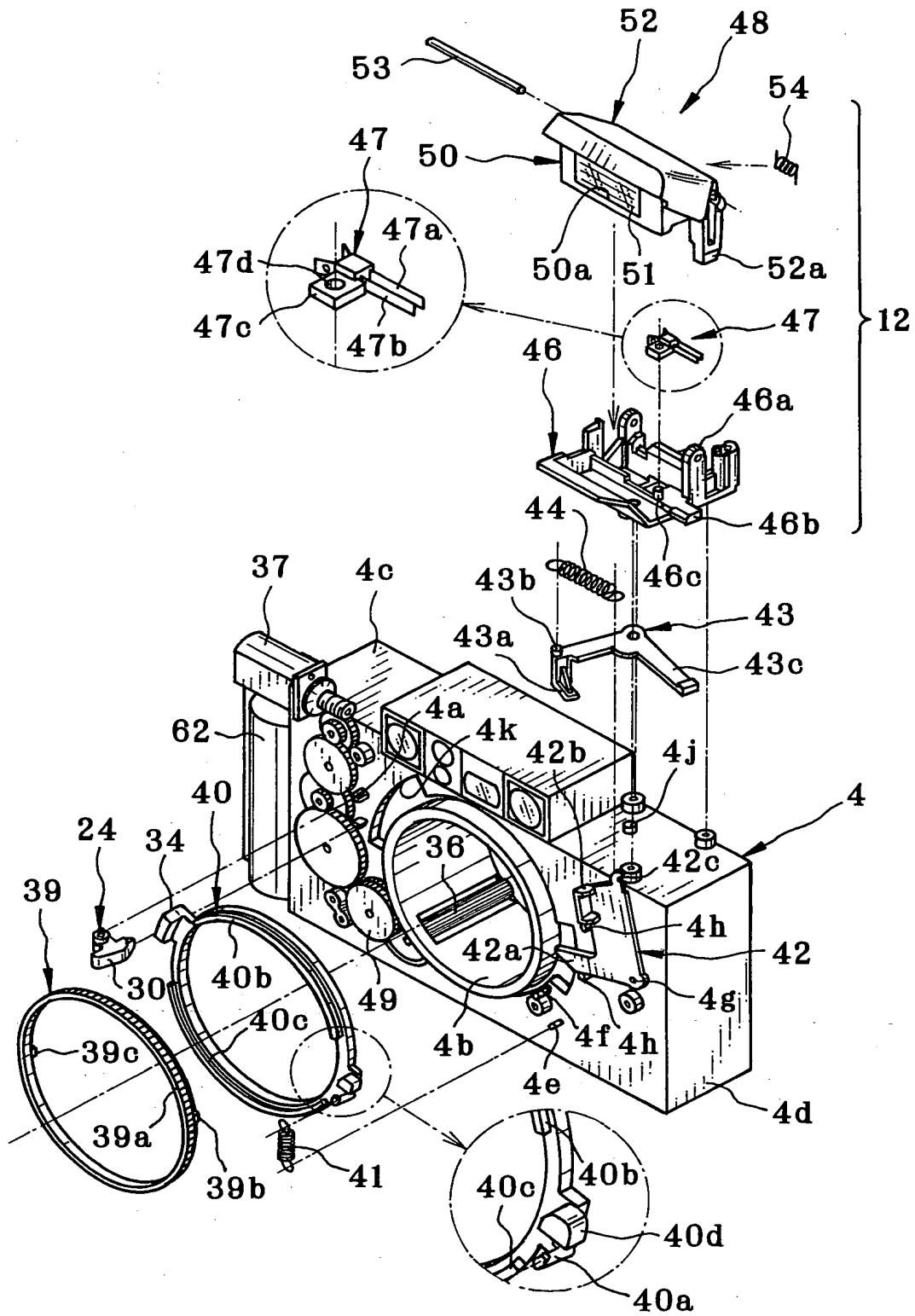


FIG. 11

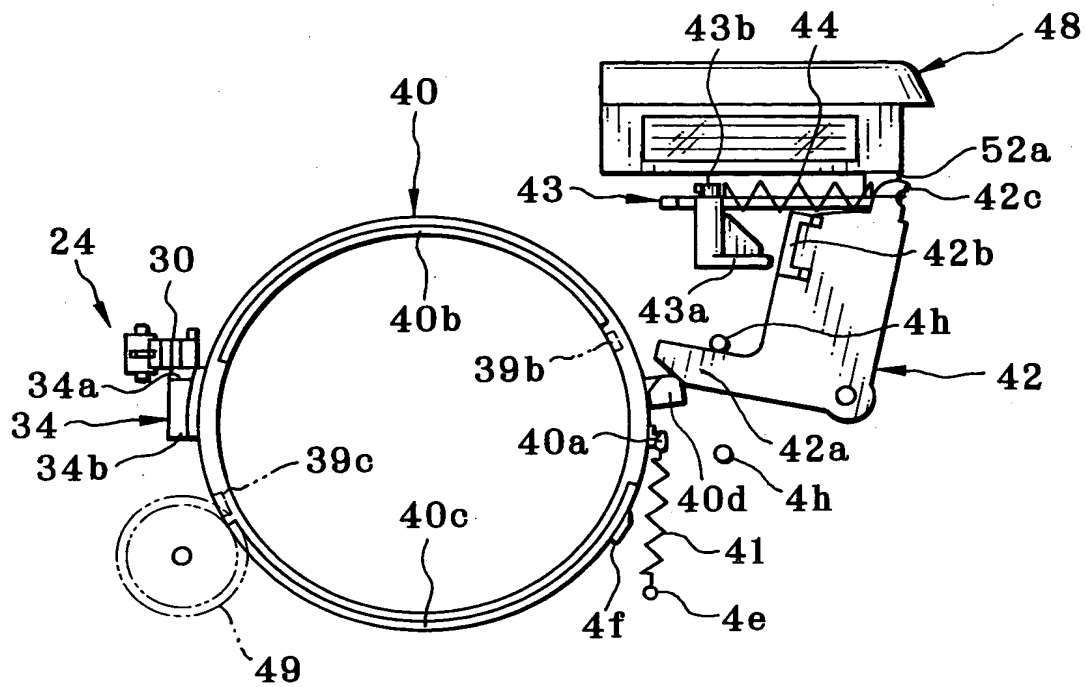


FIG. 12

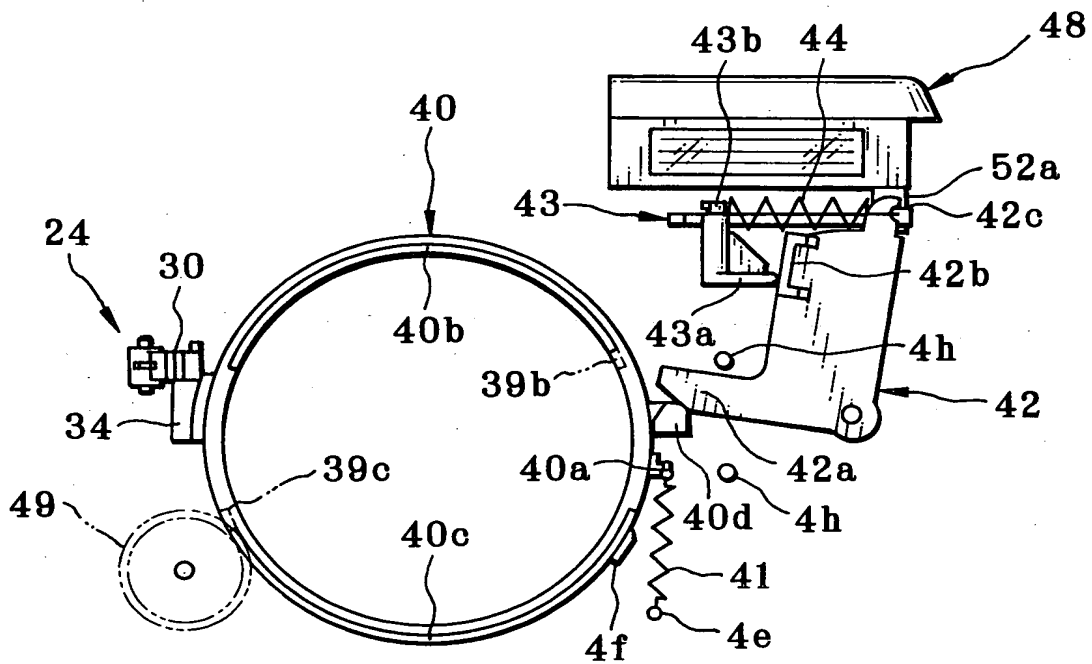


FIG. 13

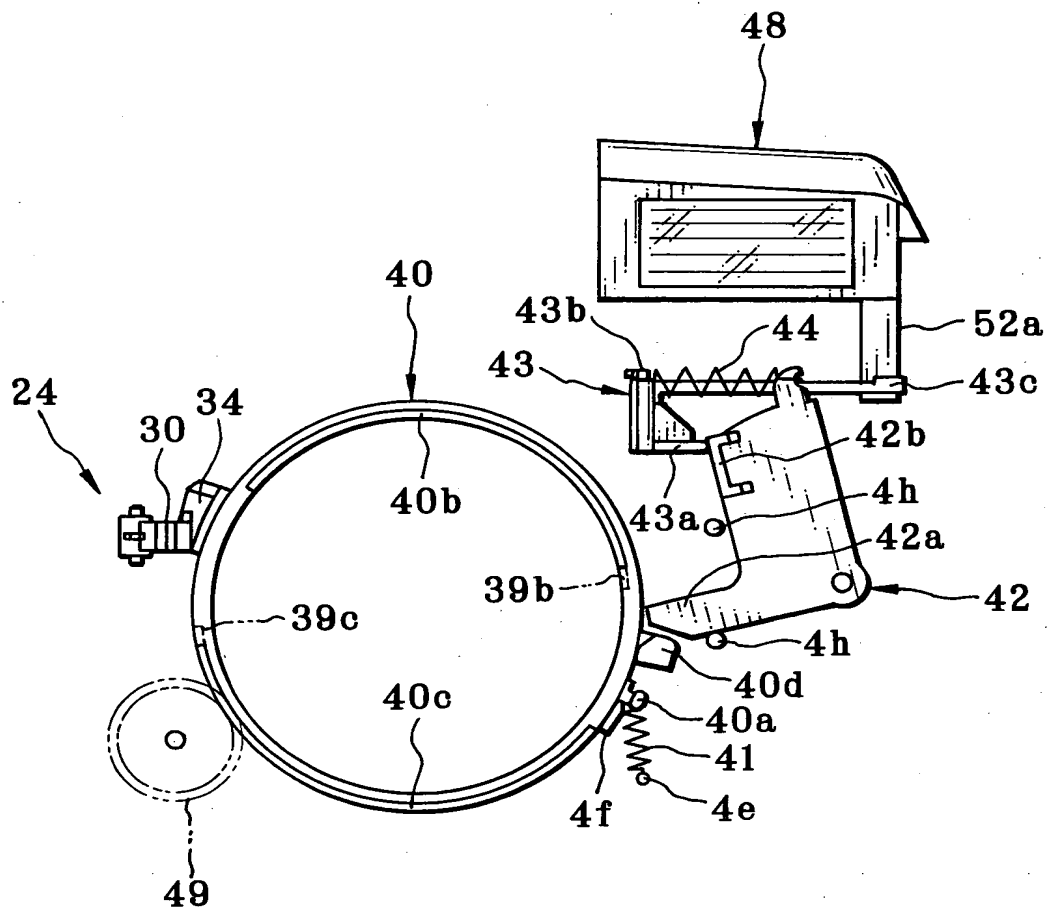


FIG. 14

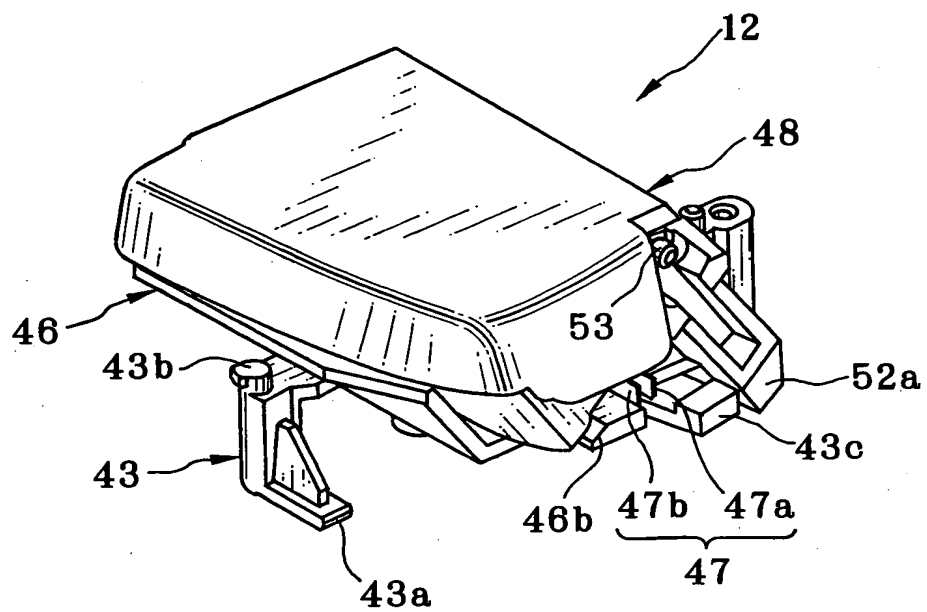


FIG. 15

